

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	24	Chen-Kuang-Chao.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:24
L3	10	Lu-Jui-Lin.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:24
L4	4	Yang-Ling-Wuu.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:24
L5	32	1 or 3 or 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:30
L6	331	(flash adj memory) and (resist or photo\$1resist or photo\$1sensitive) and (tunnel\$3 adj3 dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:24
L7	307	6 and (implant or implantation or implanting or doping or dopant or doped)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:32
L8	293	7 and @ay<="2003"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:32
L9	283	8 and (control adj3 gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:33

L10	280	9 and (float\$3 adj3 gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:34
L11	147	10 and (polish or polishing or cmp or planarize or planarizing)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 13:34
L12	275	6 and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:25
L13	267	12 and (control adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:25
L14	283	7 and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:26
L15	170	14 and side\$1wall	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:26
L16	3	15 and (float adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:26
L17	167	15 and (float\$3 adj gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:27

L18	266	9 and (etch or etching)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 14:27
S30 6	8353	(flash near4 memory) and source and drain	USPAT	OR	ON	2005/01/03 13:23
S30 7	8085	S306 and gate	USPAT	OR	ON	2004/12/30 16:38
S30 8	5776	S307 and (float\$3 adj gate)	USPAT	OR	ON	2004/12/30 16:40
S30 9	2473	S308 and (etch or etching)	USPAT	OR	ON	2004/12/30 16:40
S31 0	1747	S309 and (resist or photo\$1resist or photo\$1sensitive)	USPAT	OR	ON	2004/12/30 16:41
S31 1	1676	S310 and (implant\$3 or implantation or dope\$1 or doping or dopant)	USPAT	OR	ON	2004/12/30 16:41
S31 2	1411	S311 and (tunnel\$3)	USPAT	OR	ON	2004/12/30 16:42
S31 3	737	S312 and sidewall	USPAT	OR	ON	2004/12/30 16:42
S31 4	708	S313 and (control\$3 adj gate)	USPAT	OR	ON	2004/12/30 16:44
S31 5	694	S314 and (polysilicon or (poly\$1crystalline adj silicon))	USPAT	OR	ON	2004/12/30 16:44
S31 6	375	S315 and (cmp or polish or polishing or planarize or planarizing or (etch adj back))	USPAT	OR	ON	2004/12/30 16:46